



09/944985

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Arup Bhattacharyya Examiner: Thien Tran  
Serial No.: 09/944985 Group Art Unit: 2811  
Filed: August 30, 2001 Docket: 1303.023US1  
Title: SCALABLE FLASH/NV STRUCTURES & DEVICES WITH ENHANCED  
ENDURANCE

COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS RCE  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Applicant would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
10/075484	February 12, 2002	1303.043US1	ASYMMETRIC BAND-GAP ENGINEERED NONVOLATILE MEMORY DEVICE

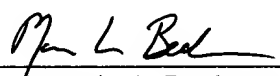
Respectfully submitted,

ARUP BHATTACHARYYA

By Applicant's Representatives,

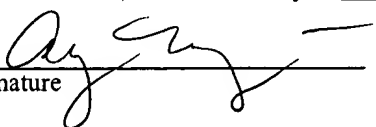
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
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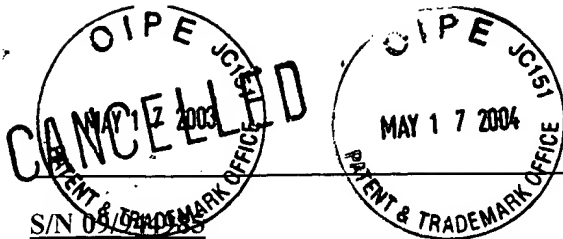
Date 5-13-04

By   
Marvin L. Beekman  
Reg. No. 38,377

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 13th day of May, 2004.

Name Amy Moriarty

Signature 



S/N 09/044985

PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Arup Bhattacharyya	Examiner:	Thien Tran
Serial No.:	09/944985	Group Art Unit:	2811
Filed:	August 30, 2001	Docket:	1303.023US1
Title:	SCALABLE FLASH/NV STRUCTURES & DEVICES WITH ENHANCED ENDURANCE		

INFORMATION DISCLOSURE STATEMENT

MS RCE  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.


Respectfully submitted,

ARUP BHATTACHARYYA

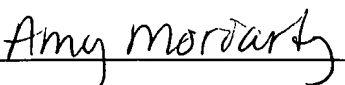
By his Representatives,

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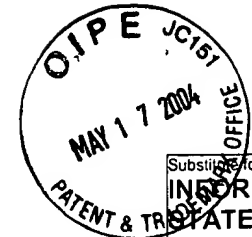
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Name 

Signature 



Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
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**CANCELLED**  
 PATENT & TRADEMARK OFFICE

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PTO/SB/08A(10-01)  
 Approved for use through 10/31/2002. OMB 851-0031  
 US Patent & Trademark Office, U.S. DEPARTMENT OF COMMERCE

Complete if Known

Application Number	09/944985
Filing Date	August 30, 2001
First Named Inventor	Bhattacharyya, Arup
Group Art Unit	2811
Examiner Name	Tran, Thien

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Attorney Docket No: 1303.023US1

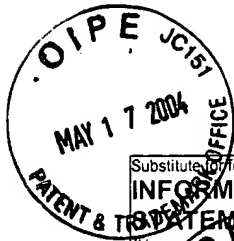
**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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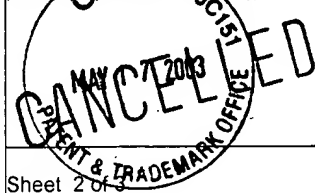
**EXAMINER**

**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)  
 \* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached



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First Named Inventor	Bhattacharyya, Arup
Group Art Unit	2811
Examiner Name	Tran, Thien

Sheet 2 of 3

Attorney Docket No: 1303.023US1

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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**EXAMINER**

**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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STATEMENT BY APPLICANT**  
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Complete if Known

<b>Application Number</b>	09/944985
<b>Filing Date</b>	August 30, 2001
<b>First Named Inventor</b>	Bhattacharyya, Arup
<b>Group Art Unit</b>	2811
<b>Examiner Name</b>	Tran, Thien

Sheet 3 of 3

Attorney Docket No: 1303.023US1

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		INUMIYA, S , et al., "Conformable formation of high quality ultra-thin amorphous Ta <sub>2</sub> O <sub>5</sub> gate dielectrics utilizing water assisted deposition (WAD) for sub 50 nm damascene metal gate MOSFETs", <u>IEDM Technical Digest. International Electron Devices Meeting</u> , (December 10-13, 2000),649-652	
		MANCHANDA, L. , "Si-doped aluminates for high temperature metal-gate CMOS: Zr-Al-Si-O, a novel gate dielectric for low power applications", <u>IEDM Technical Digest. International Electron Devices Meeting</u> , (December 10-13, 2000),23-26	
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